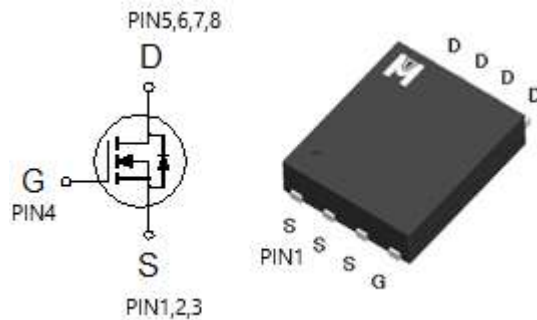


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	30V
$R_{DS(on)} (MAX.) @ V_{GS}=10V$	7.5m Ω
$R_{DS(on)} (MAX.) @ V_{GS}=4.5V$	10.5m Ω
$I_D @ T_C=25^\circ C$	50A



Single N Channel MOSFET

UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ C$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ C$	I_D	50	A
	$T_C = 100^\circ C$		35	
	$T_A = 25^\circ C$		12	
	$T_A = 70^\circ C$		10	
Pulsed Drain Current ¹		I_{DM}	140	
Avalanche Current		I_{AS}	37.5	
Avalanche Energy	$L = 0.1mH$	E_{AS}	70	mJ
Repetitive Avalanche Energy ²	$L = 0.05mH$	E_{AR}	35	
Power Dissipation	$T_C = 25^\circ C$	P_D	50	W
	$T_C = 100^\circ C$		20	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	$^\circ C$

100% UIS testing in condition of $V_D=15V, L=0.1mH, V_G=10V, I_L=25A, \text{Rated } V_{DS}=25V \text{ N-CH}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		2.5	$^\circ C / W$
Junction-to-Ambient ³	$R_{\theta JA}$		50	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

³50 $^\circ C / W$ when mounted on a 1 in² pad of 2 oz copper.



ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.4	2.0	3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	μA
		V _{DS} = 20V, V _{GS} = 0V, T _J = 125 °C			25	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	50			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 25A		6	7.5	mΩ
		V _{GS} = 4.5V, I _D = 20A		8	10.5	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 20A		18		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		1014		pF
Output Capacitance	C _{oss}			163		
Reverse Transfer Capacitance	C _{rss}			93		
Gate Resistance	R _g	V _{GS} = 15mV, V _{DS} = 0V, f = 1MHz		2.2		Ω
Total Gate Charge ^{1,2}	Q _g (V _{GS} =10V)	V _{DS} = 15V, V _{GS} = 10V, I _D = 25A		15		nC
	Q _g (V _{GS} =4.5V)			8.5		
Gate-Source Charge ^{1,2}	Q _{gs}			3.3		
Gate-Drain Charge ^{1,2}	Q _{gd}			3.5		
Turn-On Delay Time ^{1,2}	t _{d(on)}		V _{DS} = 15V, I _D = 20A, V _{GS} = 10V, R _{GS} = 2.7Ω		10	
Rise Time ^{1,2}	t _r			10		
Turn-Off Delay Time ^{1,2}	t _{d(off)}			20		
Fall Time ^{1,2}	t _f			15		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_c = 25 °C)						
Continuous Current	I _S				50	A
Pulsed Current ³	I _{SM}				140	
Forward Voltage ¹	V _{SD}	I _F = I _S , V _{GS} = 0V			1.3	V
Reverse Recovery Time	t _{rr}	I _F = I _S , dI _F /dt = 100A / μS		20		nS
Peak Reverse Recovery Current	I _{RM(REC)}			180		A
Reverse Recovery Charge	Q _{rr}			11		nC



杰力科技股份有限公司
Excelliance MOS Corporation

EMP75N03HR

¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

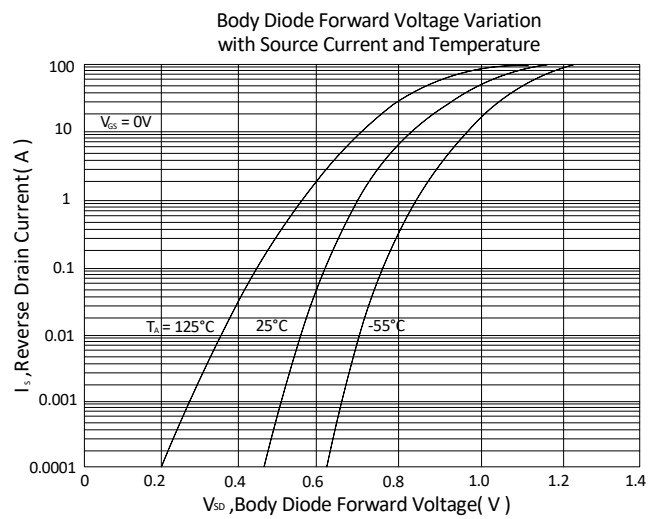
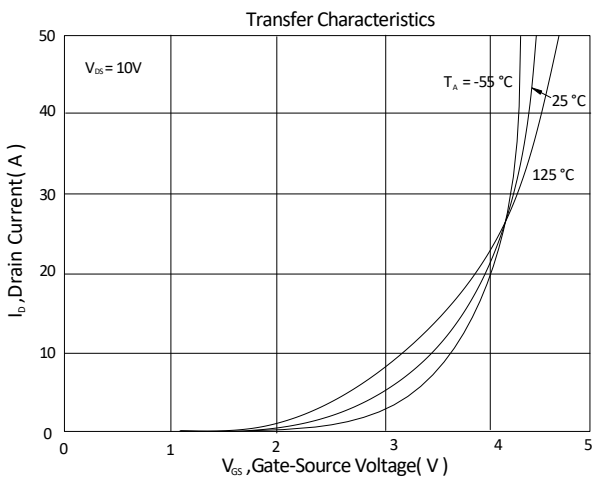
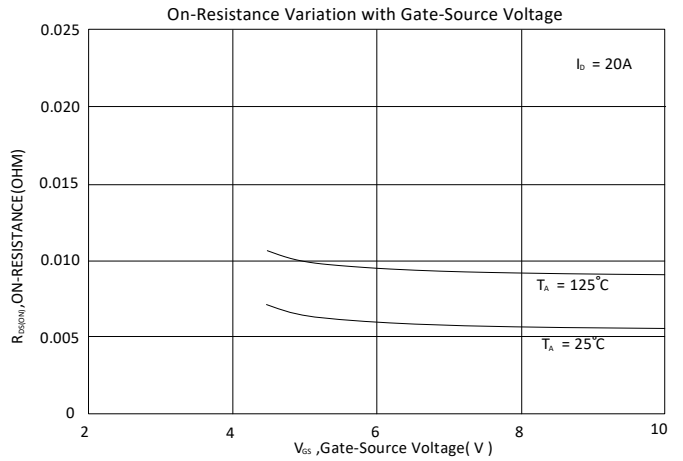
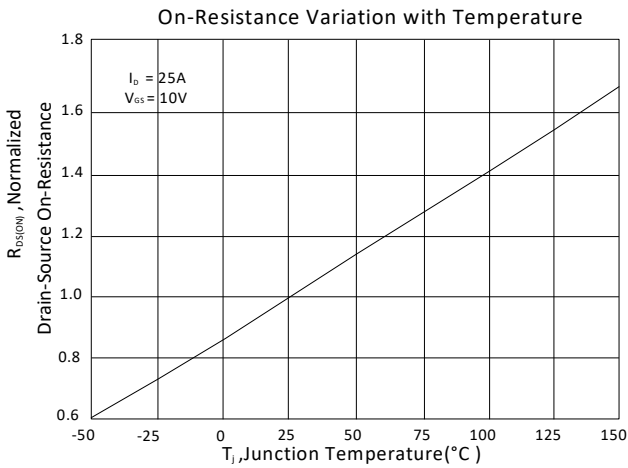
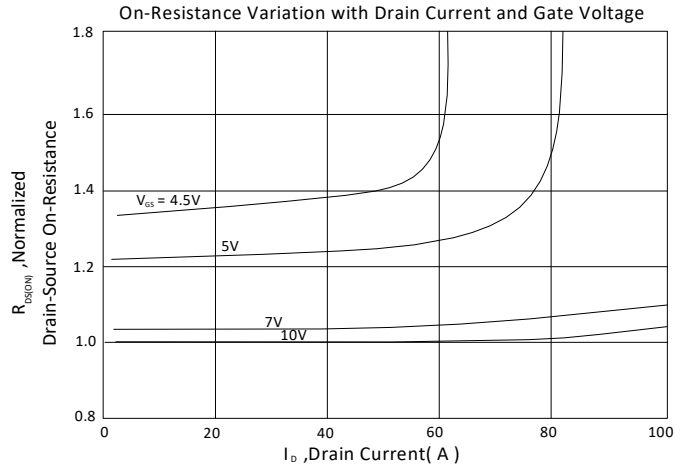
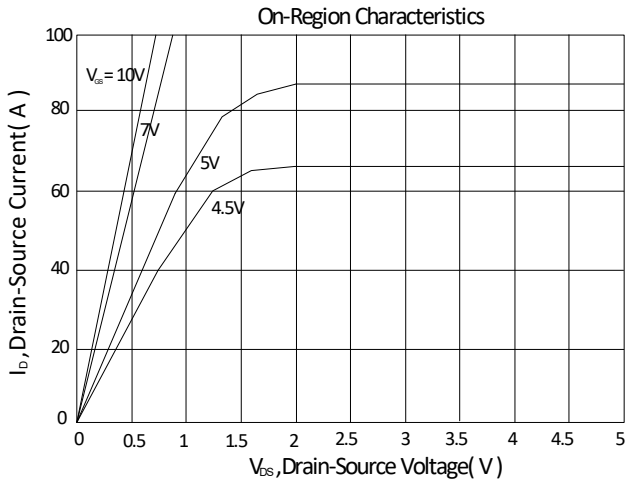
²Independent of operating temperature.

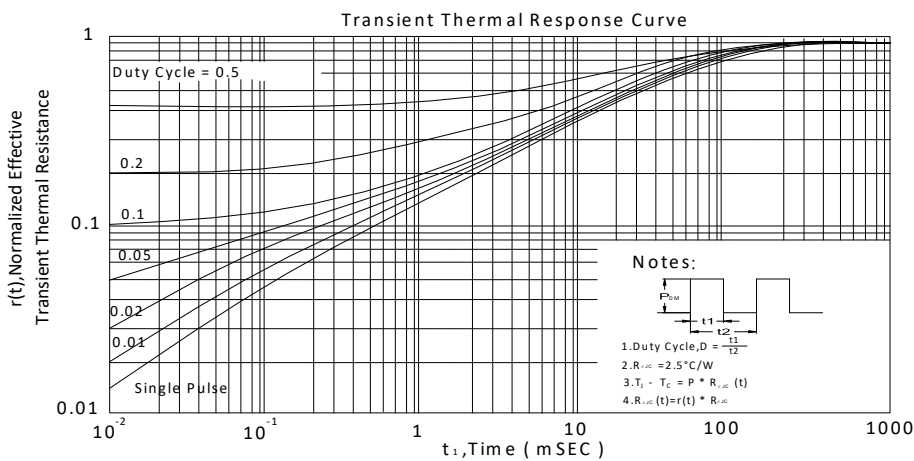
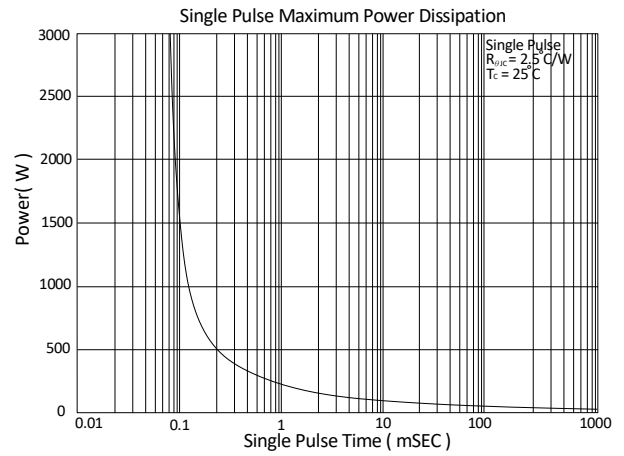
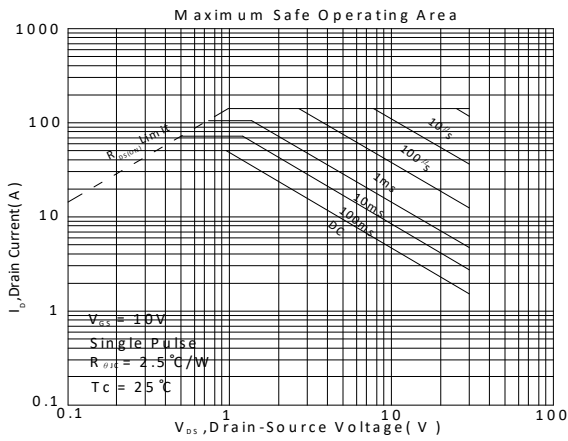
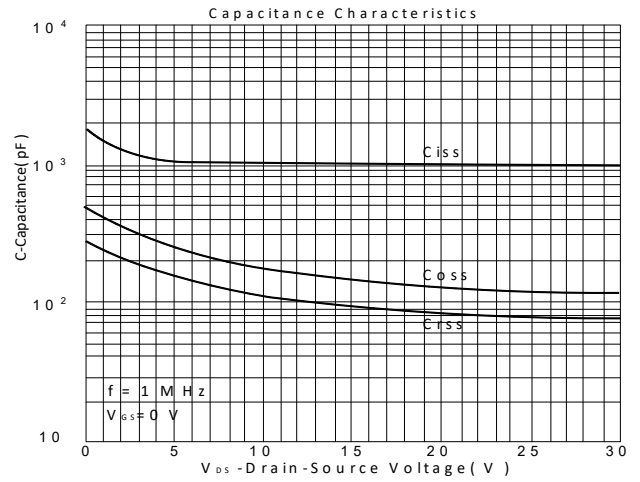
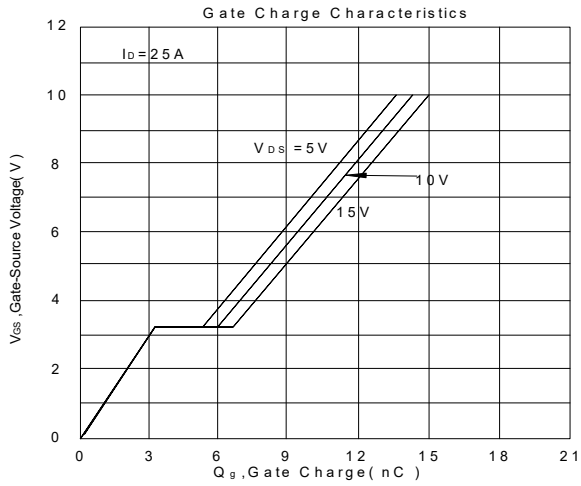
³Pulse width limited by maximum junction temperature.

EMC will review datasheet by quarter, and update new version.



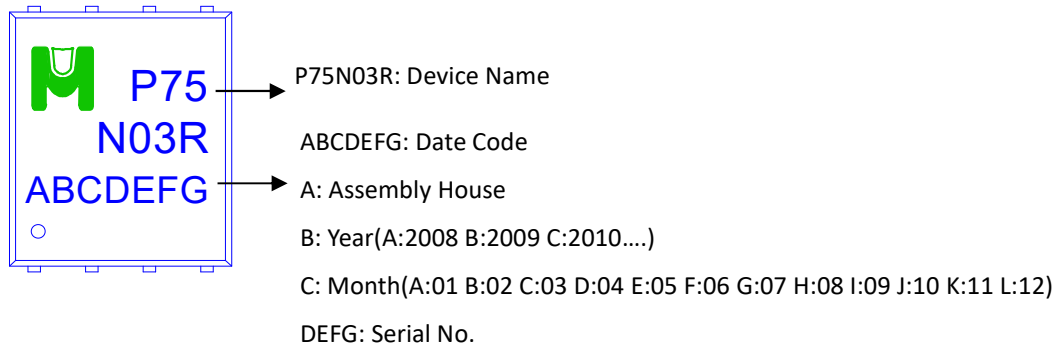
TYPICAL CHARACTERISTICS



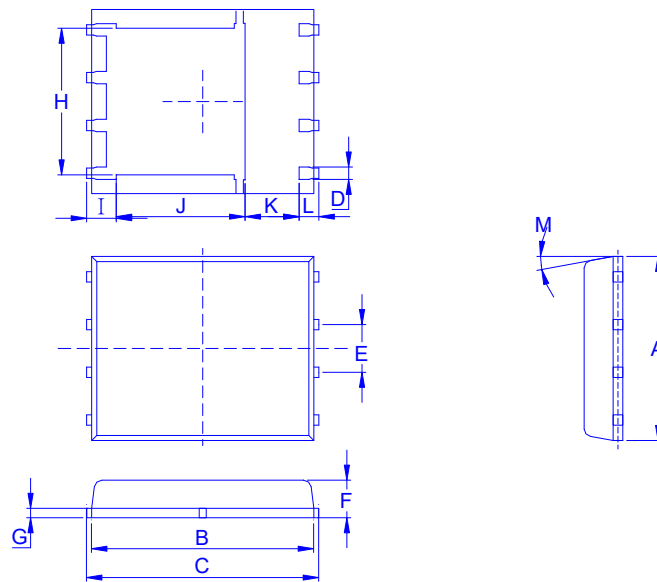


Ordering & Marking Information:

Device Name: EMP75N03HR for EDFN5X6



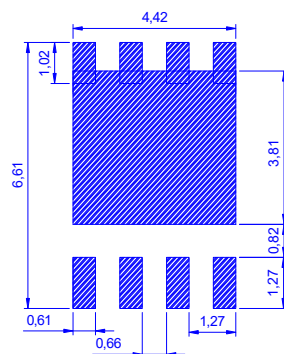
Outline Drawing



Dimension in mm

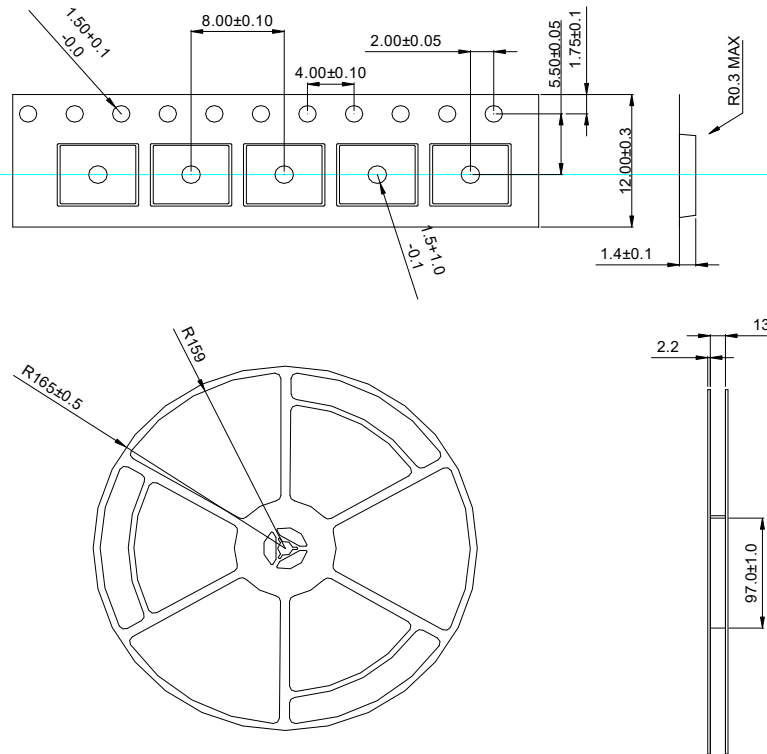
Dimension	A	B	C	D	E	F	G	H	I	J	K	L	M
Min	4.80	5.55	5.90	0.30	1.17	0.85	0.15	3.61	0.38	3.18	1.00	0.38	0°
Typ.	4.90	5.70	6.00	0.40	1.27	0.95	0.20	3.87	0.40	3.44	1.20	0.40	
Max	5.40	5.85	6.15	0.51	1.37	1.17	0.34	4.31	0.71	3.78	1.39	0.71	12°

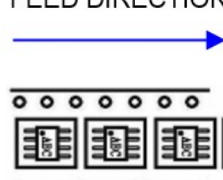
Recommended minimum pads





◆ Tape&Reel Information:2500pcs/Reel(Dimension in millimeter)



產品別	EDFN5X6
Reel 尺寸	13"
編帶方式	FEED DIRECTION 
前空格	25
後空格	50
裝箱數	
滿捲數量	2.5K
捲/內盒比	1 : 1
內盒滿箱數	2.5K
內/外箱比	10 : 1
外箱滿箱數	25K